EE-382M VLSI-II CMOS LEVEL SHIFTERS SPRING 2015

Gian Gerosa

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OUTLINE

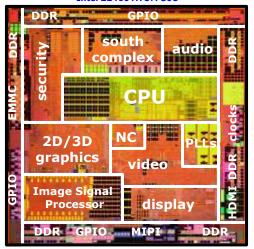
- Motivation
- Basic Operation
- Design Evolution
- Designing for Collapsible Power Grids with FIREWALLs
- Multi-stage Design for High Voltage
- Conclusion

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MOTIVATION

SoC integration of many unrelated functions in their own power 'islands'.





Rumi Zahir, HOT CHIPs #24, Aug. 2012

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MOTIVATION - cnt'd

- On-die voltage regulation leading to power 'islands' that can have different voltage levels.
- · Power management that shuts functional units off.
- Voltage-Frequency pairs; CPU's can be run in several operating points where its power supply is adjusted to reduce power:
 - lowest frequency: 100 600MHz
 - medium frequency: 700 1500MHz
 - burst frequency: 1600 2500MHz
- OFF chip drivers have to support various voltage levels whereas the controller logic is powered by a lower voltage:

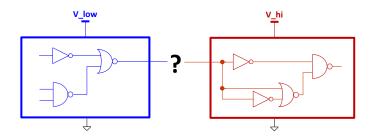
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- LPDDR: 1.25V
- MIPI-display: 1.25V regulated to 0.4V differential
- HDMI-display 3.3VSD cards: 2.85V

- GPIO: 1.25V and 1.80V

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BASIC OPERATION #1

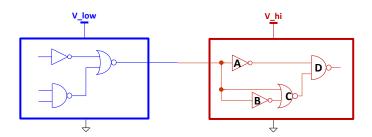


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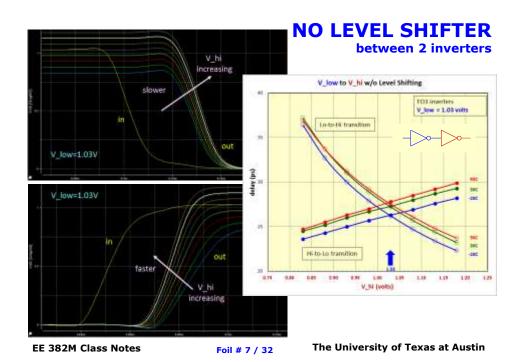
BASIC OPERATION #2



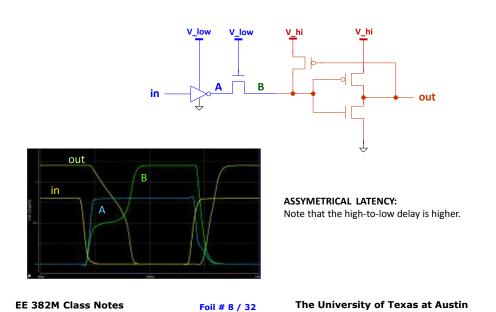
- Will this work? Assume V_low = 0.8V and V_hi = 1.2V.
- What can you say about inverters A and B, nor-gate C, nand-gate D?
- Even if you can size the gates to work correctly, what can you say about V_hi power?
- What if **V_low=1.2V** and **V_hi=0.8V**? Is this ok?

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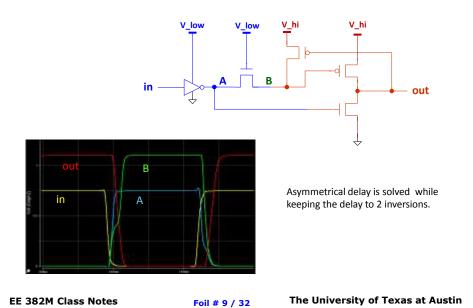
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DESIGN #1a

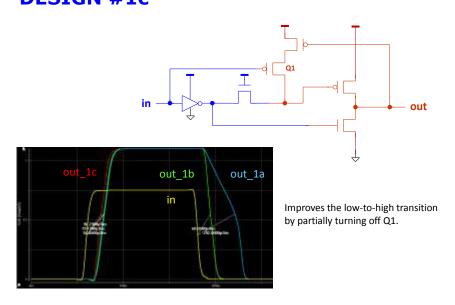


DESIGN #1b



DESIGN #1c

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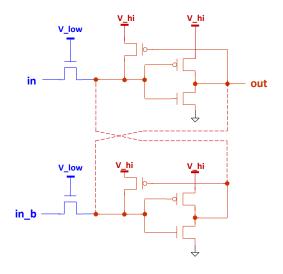


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5

DIFFERENTIAL DESIGNS -part 1-

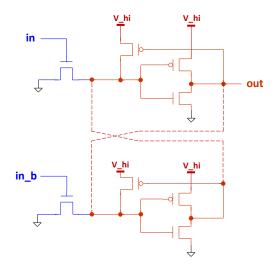


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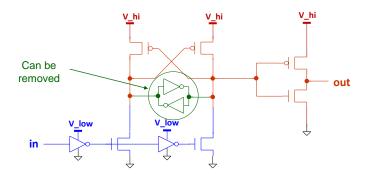
DIFFERENTIAL DESIGN -part 2-



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RE-ARRANGING leads to DESIGN #2

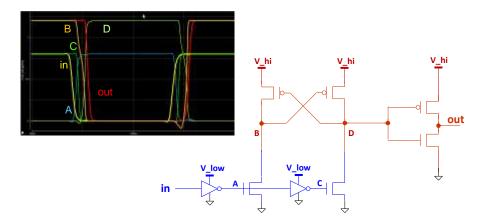


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DESIGN #2

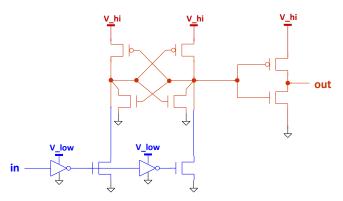


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DESIGN #3: state is preserved in **V_hi**

Add full back-to-back inverters for highest NOISE immunity at the expense of increased write-current and time to flip the latch. In addition, if the V-low power is removed, the state is preserved by the V_h i powered latch.

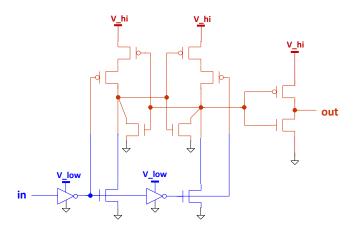


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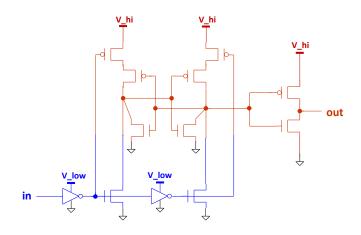
DESIGN #4a: Improving write speed



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DESIGN #4b: Improving write speed



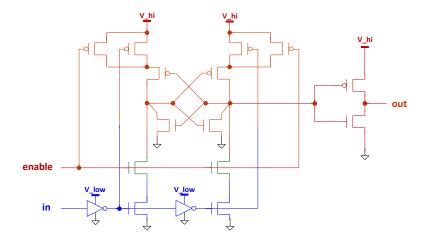
- Is the state stored in the V_hi JAM latch preserved if V_low is removed?
- Is this a better design compared to #4a?

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DESIGN #5: Preserving State

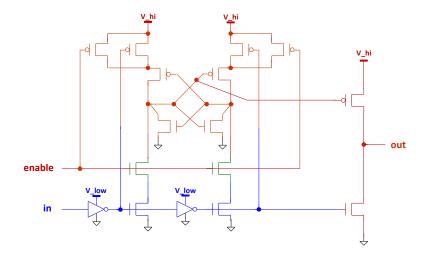


Expect this design to slow down, why? How can you make this design faster?

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DESIGN #6: Preserving State

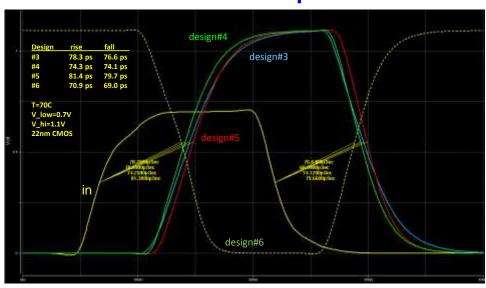


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Performance Comparison



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ADDING a FIREWALL

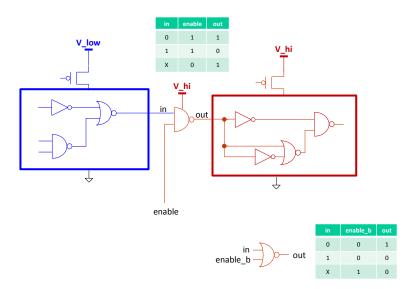
- All prior designs assumed that neither V_low nor V_hi are powered down.
- What if **V_low** is power-gated and **V_hi** remains powered up?
- What happens to the outputs of the V_low powered (blue) logic?
- Will the state of the V_hi logic be preserved (even if it remains powered up)?

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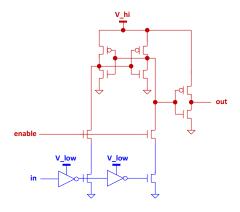
ADDING a FIREWALL



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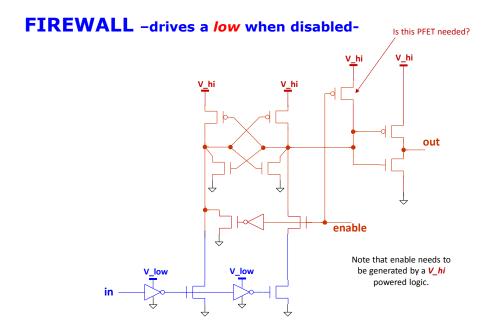
ISOLATING V_low from V_hi (what for?)



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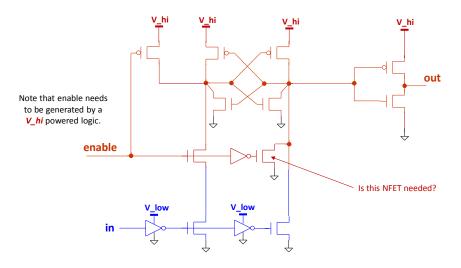
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FIREWALL -drives a high when disabled-

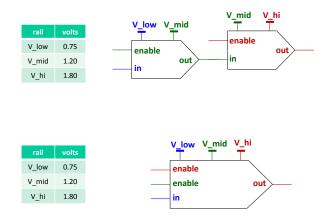


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WHAT ABOUT MUCH HIGHER V_hi?



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Multi-Stage Design

The V_hi and V_mid transistors need to be able to 'handle' the higher voltage (1.80V in this case).

Nodes D and C cannot exceed the maximum voltage that the V_low powered transistors can tolerate.

V_mid

V_low

V_low

V_low

V_low

V_low

V_low

V_low

0.75

V_mid

1.20

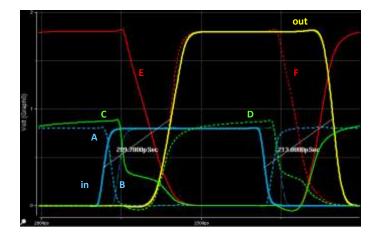
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1.80

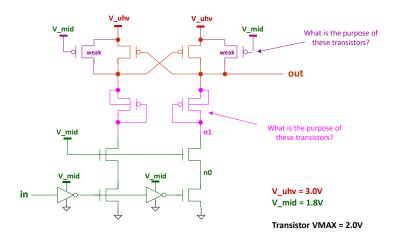
Multi-Stage Level Shifter Performance



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What About Supplies Higher Than Vmax?

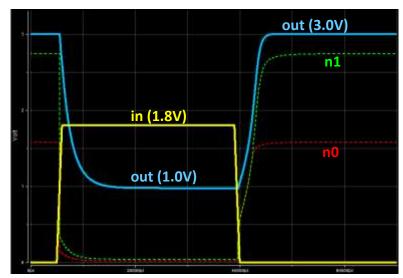


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What About Supplies Higher Than Vmax?



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SUMMARY

- Modern day mobile SoC designs contain many functions (CPU, Graphics, Memory controllers, DDR IO, Display controllers, HDMI, MIPI, Video Processing, standard voltage off-chip transceivers, etc.) which are powered by different voltages and may be power-gated to globally optimize battery life.
- Voltage level shifters are used at the IO interfaces of these functional blocks powered by different voltage levels.
- Fire-Walling is required to preserve state of those functional blocks that remain powered-up; short-circuit current reduction needs it as well (blocks X-propagation).
- Reducing level shifter latency is critical for high performance circuits.

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REFERENCES

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- Kerry Bernstein et. al., 'High Speed CMOS Design Styles', Kluwer Academic Publishers, 1999, pp. 230-233.
- 3. Chandrakasan, Bowhill, Fox, 'Design of High Performance Microprocessor Circuits', IEEE Press. P. 384.
- S.H. Kulkarni and D. Sylvester, 'Fast and Energy-Efficient Asynchronous Level Converters for Multi-VDD Design', IEEE SoC Conference, 2003, pp. 169-172.
- S. Hsu, A. Agarwal, M. Anders, S. Mathew, H. Kaul, F. Sheikh, R. Krishnamurthy, "A 280mV-to-1.1V 256b reconfigurable SIMD vector permutation engine with 2-dimensional shuffle in 22nm CMOS," 2012 IEEE International Solid-State Circuits Conference Digest of Technical Papers (ISSCC), pp.178-180, 19-23 Feb. 2012.

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